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(54) Title: KIT AND METHOD FOR PRODUCING A SEMICONDUCTOR DEVICE

(57) Abstract: An object is to provide a kit that includes a polishing fluid and a washing liquid which may enhance the flatness of a processed object and reduce the likelihood of organic residues remaining on the processed object when a processing object is subjected to chemical mechanical polishing using the kit and subsequently cleaned using the kit and a method for producing a semiconductor device in which the above kit is used. A kit used for chemical mechanical polishing of a processing object and cleaning of the processing object that has been subjected to the chemical mechanical polishing includes a polishing fluid and a washing liquid, the polishing fluid including abrasive grains and a nonionic surfactant, the polishing fluid having a pH of 7.0 or more, the washing liquid including at least one first compound selected from the group consisting of xanthine, a xanthine derivative, adenine, and an adenine derivative and at least one second compound other than the first compound, the second compound being selected from the group consisting of a secondary amine compound, a tertiary amine compound, and a quaternary ammonium compound.



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